# 74HCU04-Q100

# Hex unbuffered inverter Rev. 2 — 22 October 2015

**Product data sheet** 

#### **General description** 1.

The 74HCU04-Q100 is a hex unbuffered inverter. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### **Features and benefits** 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Complies with JEDEC standard JESD7A
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - $\bullet$  MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

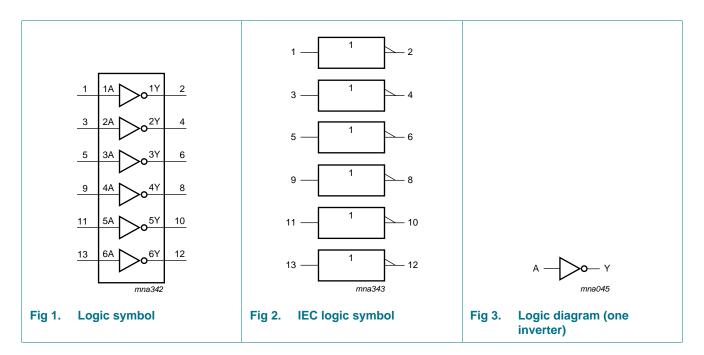
#### **Ordering information** 3.

Table 1. **Ordering information** 

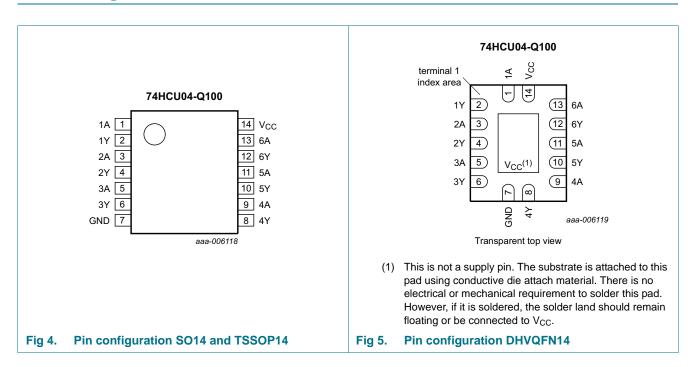
Type number	Package			
	Temperature range	Name	Description	Version
74HCU04D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74HCU04PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74HCU04BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1



### 4. Functional diagram



### 5. Pinning information



Hex unbuffered inverter

### 5.1 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1Y	2	data output
2A	3	data input
2Y	4	data output
3A	5	data input
3Y	6	data output
GND	7	ground (0 V)
4Y	8	data output
4A	9	data input
5Y	10	data output
5A	11	data input
6Y	12	data output
6A	13	data input
V <sub>CC</sub>	14	supply voltage

### 6. Functional description

#### Table 3. Function table

H = HIGH voltage level; L = LOW voltage level

Input	Output
nA	nY
L	Н
Н	L

## 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC}$	supply voltage			-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	[1]	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	[1]	-	±50	mA
I <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±25	mA
I <sub>CC</sub>	supply current			-	50	mA
I <sub>GND</sub>	ground current			-50	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation		[2]			
	SO14, TSSOP14 and DHVQFN14 packages			-	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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[2] For SO14 package:  $P_{tot}$  derates linearly with 8 mW/K above 70 °C. For TSSOP14 packages:  $P_{tot}$  derates linearly with 5.5 mW/K above 60 °C. For DHVQFN14 packages:  $P_{tot}$  derates linearly with 4.5 mW/K above 60 °C.

### 8. Recommended operating conditions

#### Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	V
VI	input voltage		0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C

### 9. Static characteristics

#### Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.7	1.4	-	1.7	-	1.7	-	V
	input voltage	V <sub>CC</sub> = 4.5 V	3.6	2.6	-	3.6	-	3.6	-	V
		V <sub>CC</sub> = 5.5 V	4.8	3.4	-	4.8	-	4.8	-	V
$V_{IL}$	LOW-level	V <sub>CC</sub> = 2.0 V	-	0.6	0.3	-	0.3	-	0.3	V
	input voltage	V <sub>CC</sub> = 4.5 V	-	1.9	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	2.6	1.2	-	1.2	-	1.2	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.8	2.0	-	1.8	-	1.8	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.0	4.5	-	4.0	-	4.0	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.5	6.0	-	5.5	-	5.5	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.2	-	0.2	-	0.2	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.5	-	0.5	-	0.5	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.5	-	0.5	-	0.5	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	2	-	20	-	20	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

### 10. Dynamic characteristics

#### Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 7.

Symbol	Parameter	Conditions		25	°C	–40 °C to +85 °C	-40 °C to +125 °C	Unit
				Тур	Max	Max	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 6	[1]					
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		19	70	90	105	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		7	14	18	21	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		5	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		6	12	15	18	ns
t <sub>t</sub>	transition time	see Figure 6	[2]					
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		19	75	95	110	ns
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		7	15	19	22	ns
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		6	13	16	19	ns
C <sub>PD</sub>	power dissipation capacitance	per inverter; $V_I = GND$ to $V_{CC}$	[3]	10	-			pF

- [1]  $t_{pd}$  is the same as  $t_{PHL}$ ,  $t_{PLH}$ .
- [2]  $t_t$  is the same as  $t_{THL}$ ,  $t_{TLH}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o$  = output frequency in MHz;

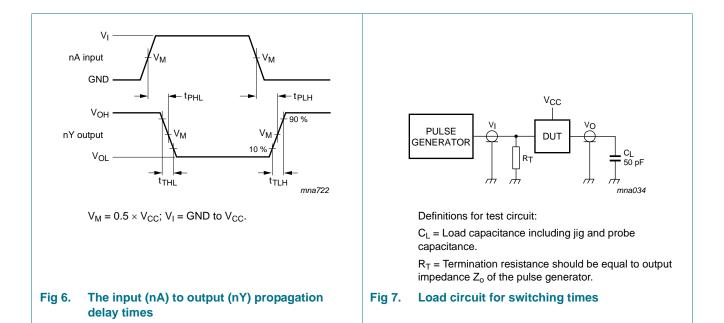
 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

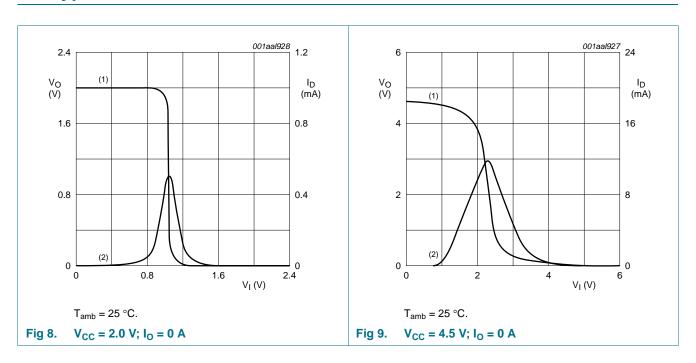
N = number of inputs switching;

 $\Sigma (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

#### 11. Waveforms



### 12. Typical transfer characteristics



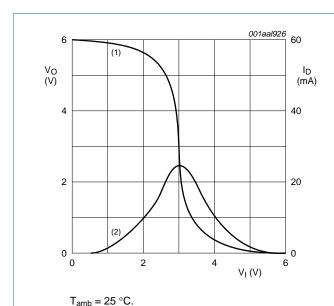
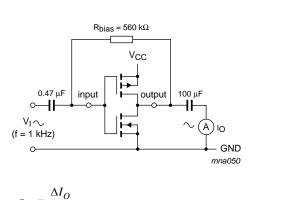


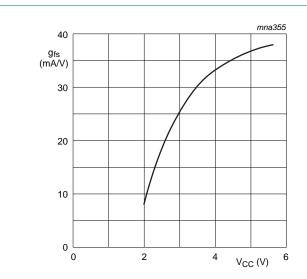
Fig 10.  $V_{CC} = 6.0 \text{ V}$ ;  $I_{O} = 0 \text{ A}$ 



$$g_{fs} = \frac{\Delta I_C}{\Delta V_I}$$

 $f_i = 1 \text{ kHz at } V_O \text{ is constant}$ 

Fig 11. Test set-up for measuring forward transconductance



 $T_{amb}$  = 25 °C.

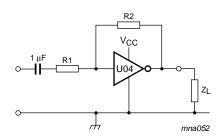
Fig 12. Typical forward transconductance as a function of the supply voltage

### 13. Application information

Some applications are:

- Linear amplifier (see Figure 13)
- Crystal oscillator design (see Figure 14)
- Astable multivibrator (see Figure 15)

Remark: All values given are typical unless otherwise specified.



Maximum  $V_{o(p-p)} = V_{CC} - 2.0 \text{ V}$  centered at  $0.5 \times V_{CC}$ .

$$G_v = -\frac{G_{ol}}{I + \frac{RI}{R2}(I + G_{ol})}$$

Gol = open loop gain

G<sub>v</sub> = voltage gain

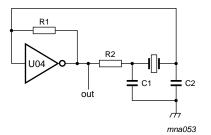
 $R1 \geq 3~k\Omega,~R2 \leq 1~M\Omega$ 

 $Z_L > 10 \text{ k}\Omega$ ;  $G_{ol} = 20 \text{ (typical)}$ 

 $V_{CC} = 6.0 \text{ V}$ 

Typical unity gain bandwidth product is 5 MHz.

Fig 13. Used as a linear amplifier



C1 = 47 pF (typical)

C2 = 33 pF (typical)

R1 = 1 M $\Omega$  to 10 M $\Omega$  (typical

R2 optimum value depends on the frequency and required stability against changes in  $V_{CC}$  or average minimum  $I_{CC}$ .  $I_{CC}$  is typically 5 mA at  $V_{CC}$  = 5 V and  $f_i$  = 10 MHz.

Fig 14. Crystal oscillator configuration

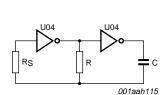
#### Table 8. External components for resonator (f < 1 MHz)

All values given are typical and must be used as an initial set-up.

Frequency	R1	R2	C1	C2
10 kHz to 15.9 kHz	22 MΩ	220 kΩ	56 pF	20 pF
16 kHz to 24.9 kHz	22 MΩ	220 kΩ	56 pF	10 pF
25 kHz to 54.9 kHz	22 MΩ	100 kΩ	56 pF	10 pF
55 kHz to 129.9 kHz	22 MΩ	100 kΩ	47 pF	5 pF
130 kHz to 199.9 kHz	22 ΜΩ	47 kΩ	47 pF	5 pF
200 kHz to 349.9 kHz	10 ΜΩ	47 kΩ	47 pF	5 pF
350 kHz to 600 kHz	10 ΜΩ	47 kΩ	47 pF	5 pF

Table 9. Optimum value for R2

Frequency	R2	Optimum for
3 kHz	2.0 kΩ	minimum required I <sub>CC</sub>
	8.0 kΩ	minimum influence due to change in V <sub>CC</sub>
6 kHz	1.0 kΩ	minimum required I <sub>CC</sub>
	4.7 kΩ	minimum influence by V <sub>CC</sub>
10 kHz	0.5 kΩ	minimum required I <sub>CC</sub>
	2.0 kΩ	minimum influence by V <sub>CC</sub>
14 kHz	0.5 kΩ	minimum required I <sub>CC</sub>
	1.0 kΩ	minimum influence by V <sub>CC</sub>
>14 kHz	-	replace R2 by C3 with a typical value of 35 pF

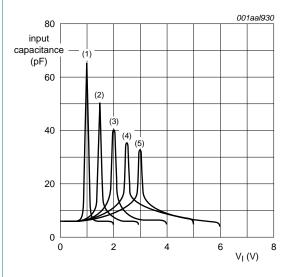


$$f = \frac{I}{T} \approx \frac{I}{2.2RC}$$

$$R_S \approx 2 \times R$$

The average I<sub>CC</sub> (mA) is approximately  $3.5 + 0.05 \times f$  (MHz)  $\times$  C (pF) at V<sub>CC</sub> = 5.0 V.





 $V_{CC} = 2.0 \text{ V}$ 

 $V_{CC} = 3.0 \text{ V}$ 

 $V_{CC} = 4.0 \text{ V}$ 

V<sub>CC</sub> = 5.0 V

V<sub>CC</sub> = 6.0 V

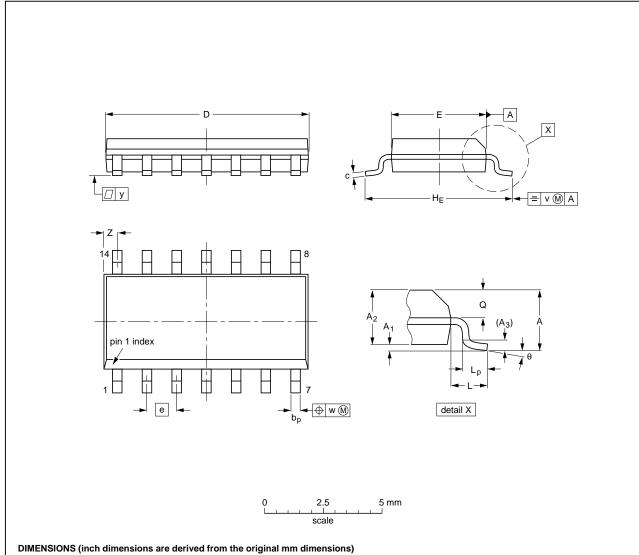
 $T_{amb} = 25 \, ^{\circ}C.$ 

Fig 16. Input capacitance as function of input voltage

### 14. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19

Fig 17. Package outline SOT108-1 (SO14)

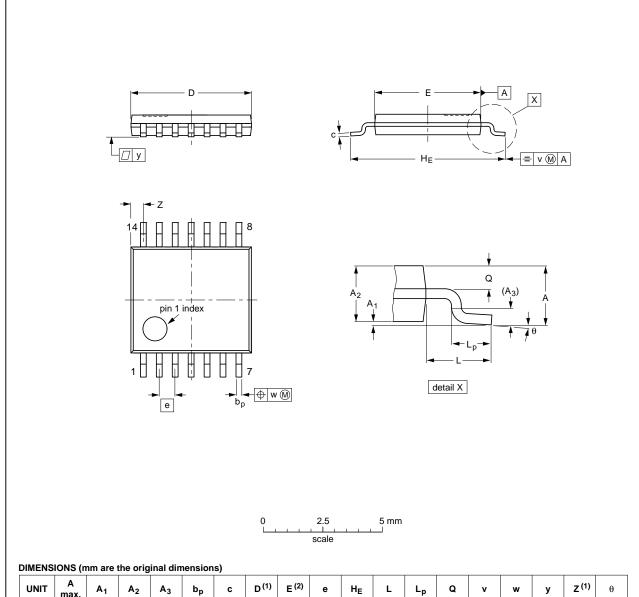
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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



						-,												
UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT402-1		MO-153				<del>99-12-27</del> 03-02-18

Fig 18. Package outline SOT402-1 (TSSOP14)

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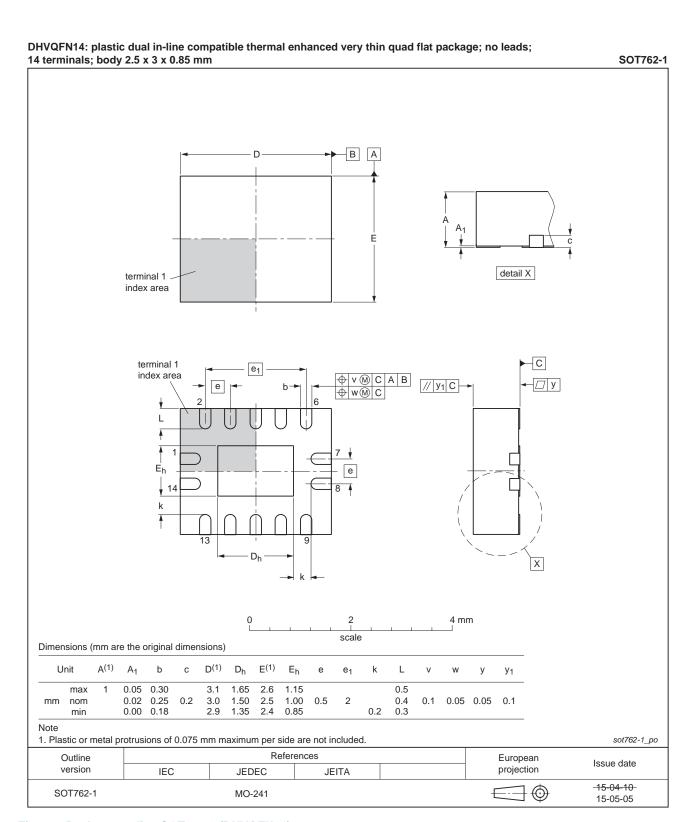


Fig 19. Package outline SOT762-1 (DHVQFN14)

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Hex unbuffered inverter

### 15. Abbreviations

#### Table 10. Abbreviations

Acronym	Description	
CMOS	Complementary Metal Oxide Semiconductor	
LSTTL	Low-power Schottky Transistor-Transistor Logic	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
MIL	Military	
TTL	Transistor-Transistor Logic	

## 16. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HCU04_Q100 v.2	20151022	Product data sheet	-	74HCU04_Q100 v.1
Modifications:	<ul> <li>Conditions V<sub>IL</sub> and V<sub>IH</sub> corrected (errata).</li> </ul>			
74HCU04_Q100 v.1	20130131	Product data sheet	-	-

### 17. Legal information

#### 17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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For sales office addresses, please send an email to: salesaddresses@nxp.com

#### Hex unbuffered inverter

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